

## ABSTRACT

The present disclosure provides a semiconductor structure and a manufacturing method therefor. The semiconductor structure includes: a substrate; a first insulating dielectric layer disposed on the substrate; a front layer structure disposed in the first insulating dielectric layer; 5 a second insulating dielectric layer disposed on the first insulating dielectric layer; a third insulating dielectric layer disposed on the second insulating dielectric layer; a current layer structure disposed in the third insulating dielectric layer, including a plurality of first conductive wires spaced apart from each other; a first interconnection structure passing through the second insulating dielectric layer to connect a portion of the first conductive wires 10 and the front layer structure; and a second interconnection structure passing through the first insulating dielectric layer and the second insulating dielectric layer to connect a portion of the first conductive wires, the first interconnection structure and the second interconnection structure being isolated from each other.

[Fig. 1]